

P-Channel Enhancement MOSFET

FEATURES

- \cdot RDS(ON)<140m Ω @VGS=-2.5V
- \cdot RDS(ON)<110m Ω @VGS=-4.5V
- · TrenchFET Power MOSFET



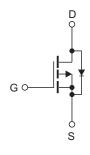
Product Summary				
Vos	$R_{DS(on)}(m\Omega)Typ$	I _D (A)	Qg (Typ)	
-20V	89 @- 2. 5V	-2	3. 3nc	
201	64 @ -4.5V	-3	3. 3110	

MECHANICAL DATA

- · Case:SOT-23(TO-236)
- * Terminals:Plated solderable per MIL-STD-750,method 2026
- · Mounting Position: Any







P-channel MOSFET

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameters	Symbol	Value	Unit
Drain-Source voltage	Vos	-20	V
Gate-Source Voltage	Vgs	±12	V
Continuous Drain Current(T」. =150℃)	ΙD	-2. 3	А
Maximum Power Dissipation @T₄=25℃	P□	1	W
Junction and Storge Temperature Range	TJ,TSTG	-55 to +150	°C

Thermal Resistance Ratings

Parameters	Symbol	Тур	Max	Unit
Junction to Ambient, Steady State 2)	R θ ЈА	-	104	°C/W

^{2.}Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.



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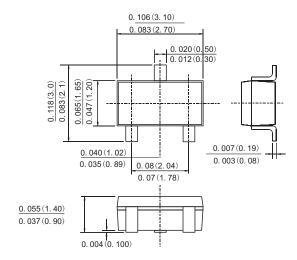
Electrical Characteristics (TJ=25°C unless otherwise noted)

Parameters	Symbol	Conditions	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	BVDSS	Vgs= 0V, In=-250μA	-20	-	-	V
Zero Gate Voltage Drain Current	Inss	VDS=-20V,VGS=0V,TC=25°C	-	-	-1	μΑ
Gate-Source Leakage Current	Igss	Vgs= 12V, Vps=0V	-	-	100	nA
Gate-Source Threshold Voltage	VGS(th)	V _{DS} = V _{GS} , I _D =-250μA	-0.4	-0.7	-1	V
Drain-Source On-State Resistance	Rds(on)	Ves=-4.5V, ID=-3A	-	64	110	- mΩ
Brain Gource on Glate Resistance	1103(011)	Vgs= -2.5V, Ip=-2A	-	89	140	
Dynamic						
Input Capacitance	Ciss		-	405	-	pF
Output Capacitance	Coss	V _D s=-10V,V _G s=0V,f=1MHz	-	75	-	
Reverse Transfer Capacitance	Crss		-	55	-	
Total Gate Charge	Qg		-	3.3	12	nc
Gate-Source Charge	Qgs	VDS=-10V,VGS=-2.5V,ID=-3A	-	0.7	-	
Gate-Drain Charge	Qgd		-	1.3	-	
Turn-on Delay Time	tD(on)		-	11	-	
Turn-On Rise Time	tr	Vgs=-4.5V,Vdd=-10V,Id=-1A,	-	35	-	ns
Turn-off Delay Time	tD(off)	Rgen=10Ω	-	30	-	
Turn-Off Fall Time	tr		-	10	-	
Drain-Source Body Diode Characteristic	3					
Maximum Body-Diode Continuous Current	Is		-	-	-1.3	Α
Diode Forward Voltage	Vsp	Is=-1.3A,Vgs=0V	-	-	-1.2	V



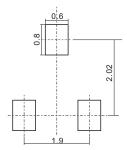
PACKAGE OUTLINE DIMENSIONS

SOT-23



Dimensions in inches and (millimetrers)

Suggested Pad Layout



Dimensions in millimetrers



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